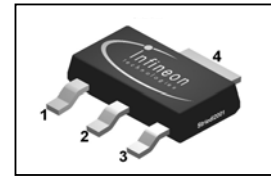


**SIPMOS® Small-Signal-Transistor**
**Features**

- P-Channel
- Enhancement mode
- Logic level
- Avalanche rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101


**Product Summary**

$V_{DS}$	-100	V
$R_{DS(on),max}$	800	mΩ
$I_D$	-1	A


**PG-SOT-223**


Type	Package	Tape and Reel Information	Marking	Lead free	Packing
BSP322P	PG-SOT-223	L6327: 1000 pcs/reel	BSP322P	Yes	Non dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	1	A
		$T_C=70\text{ °C}$	0.8	
Pulsed drain current	$I_{D,pulse}$	$T_C=25\text{ °C}$	4	
Avalanche energy, single pulse	$E_{AS}$	$I_D=-1\text{ A}$ , $R_{GS}=25\text{ Ω}$	57	mJ
Gate source voltage	$V_{GS}$		±20	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	1.8	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... 150	°C
ESD Class		JESD22-A114-HBM	1A (250V to 500V)	
Soldering temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint, steady state	-	-	115	K/W
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , steady state	-	-	70	

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=-250\text{ }\mu\text{A}$	-100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-380\text{ }\mu\text{A}$	-2.0	-1.5	-1.0	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	-0.1	-1	$\mu\text{A}$
		$V_{DS}=-100\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ }^\circ\text{C}$	-	-10	-100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$	-	-10	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10\text{ V}, I_D=-1\text{ A}$	-	600	800	m $\Omega$
		$V_{GS}=-4.5\text{ V}, I_D=-0.93\text{ A}$	-	808	1000	
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=-0.8\text{ A}$	0.7	1.4	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=-25\text{ V},$ $f=1\text{ MHz}$	-	280	372	pF
Output capacitance	$C_{oss}$		-	70	94	
Reverse transfer capacitance	$C_{rss}$		-	34	51	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-50\text{ V}, V_{GS}=-$ $10\text{ V}, I_D=-1\text{ A}, R_G=6\ \Omega$	-	4.6	6.9	ns
Rise time	$t_r$		-	4.3	6.5	
Turn-off delay time	$t_{d(off)}$		-	21.2	31.8	
Fall time	$t_f$		-	8.3	12.5	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=-80\text{ V}, I_D=-1\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	0.8	1.0	nC
Gate to drain charge	$Q_{gd}$		-	4.3	6.4	
Gate charge total	$Q_g$		-	12.4	16.5	
Gate plateau voltage	$V_{plateau}$		-	2.9	-	V

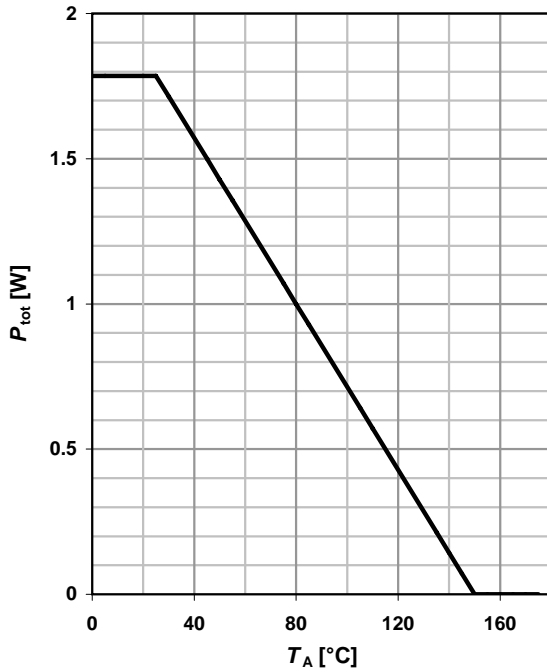
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	-1.0	A
Diode pulse current	$I_{S,pulse}$		-	-	-4.0	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-1\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.84	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=50\text{ V}, I_F= I_S ,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	47	-	ns
Reverse recovery charge	$Q_{rr}$		-	84	-	nC

<sup>2)</sup> See figure 16 for gate charge parameter definition

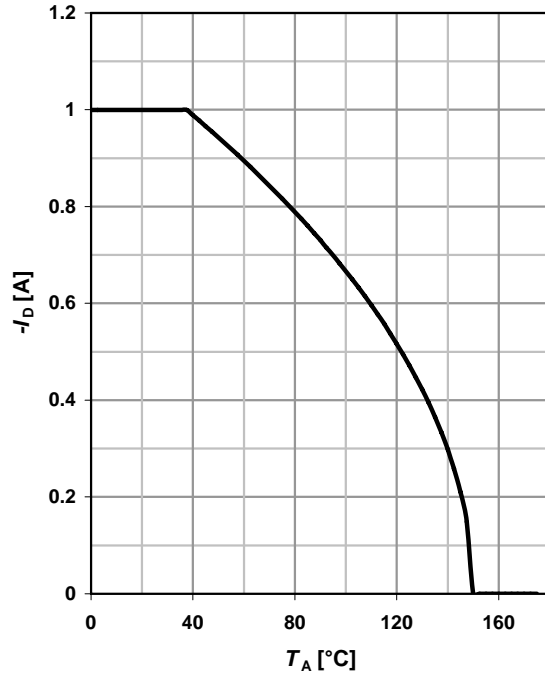
**1 Power dissipation**

$$P_{\text{tot}} = f(T_C)$$



**2 Drain current**

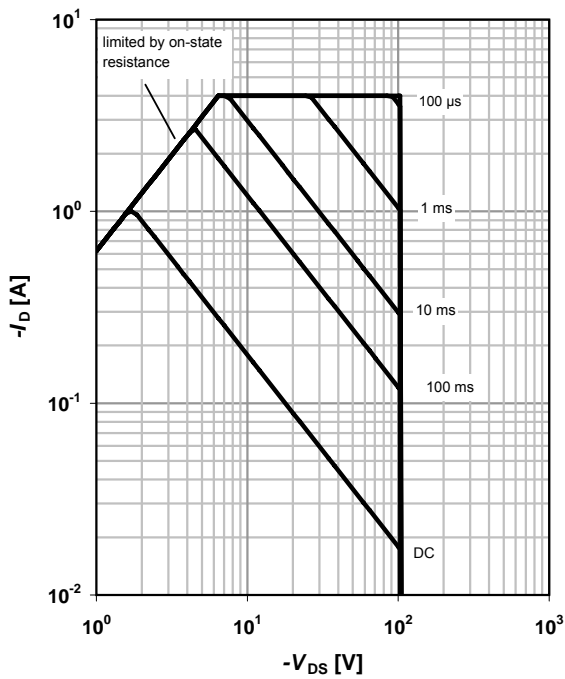
$$I_D = f(T_C); |V_{GS}| \geq 10 \text{ V}$$



**3 Safe operating area**

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

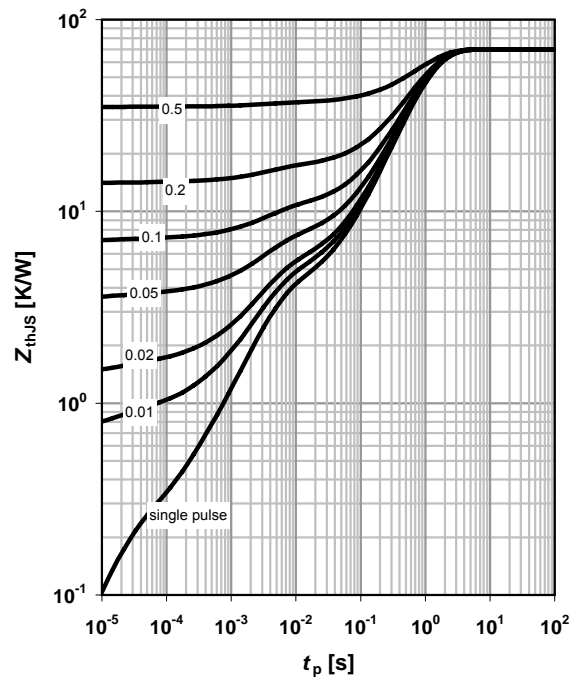
parameter:  $t_p$



**4 Max. transient thermal impedance**

$$Z_{\text{thJC}} = f(t_p)$$

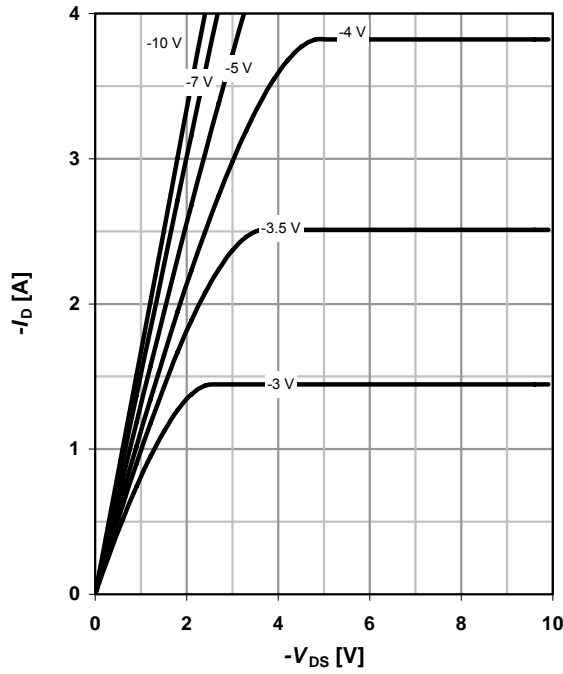
parameter:  $D = t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

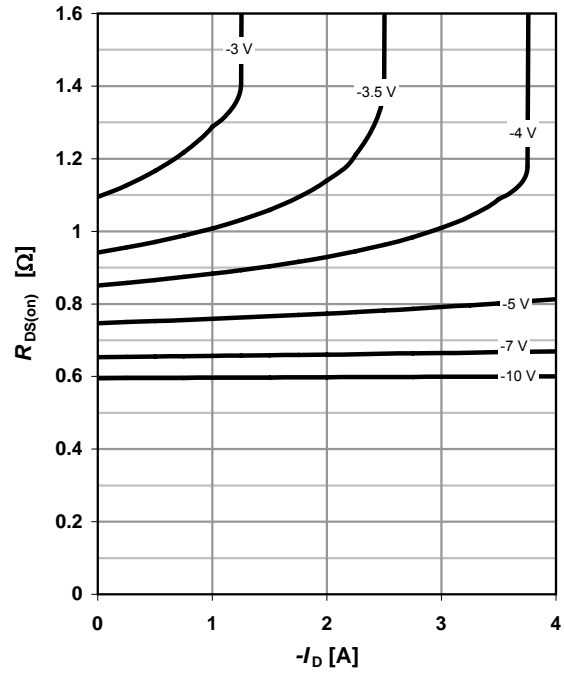
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

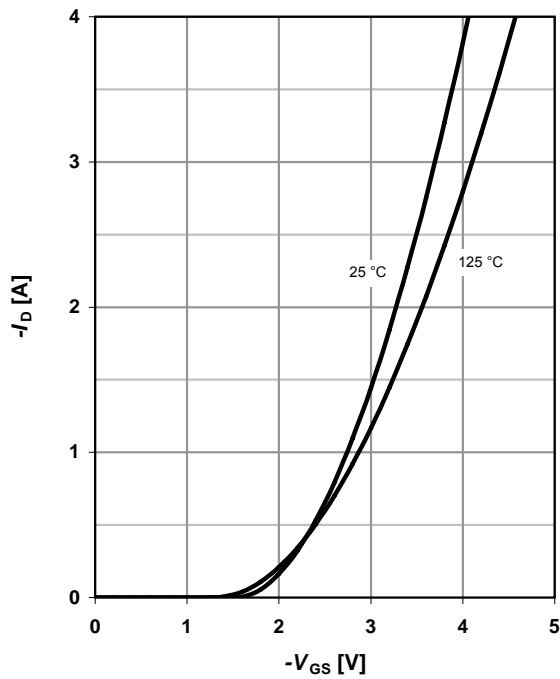
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

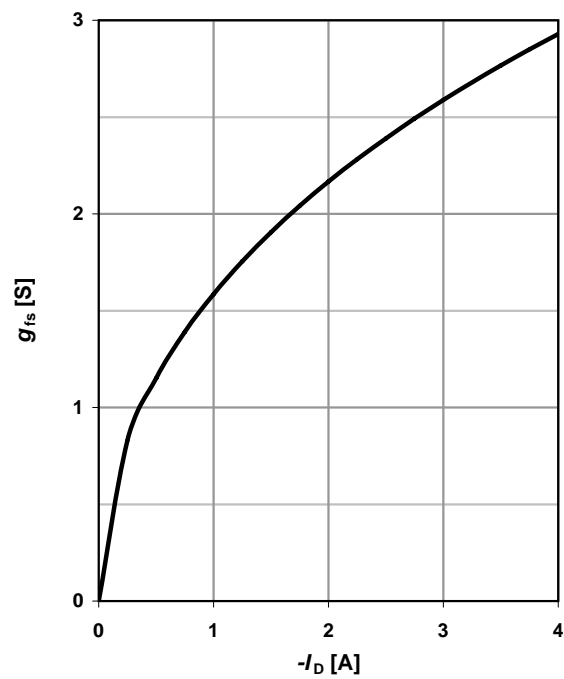
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



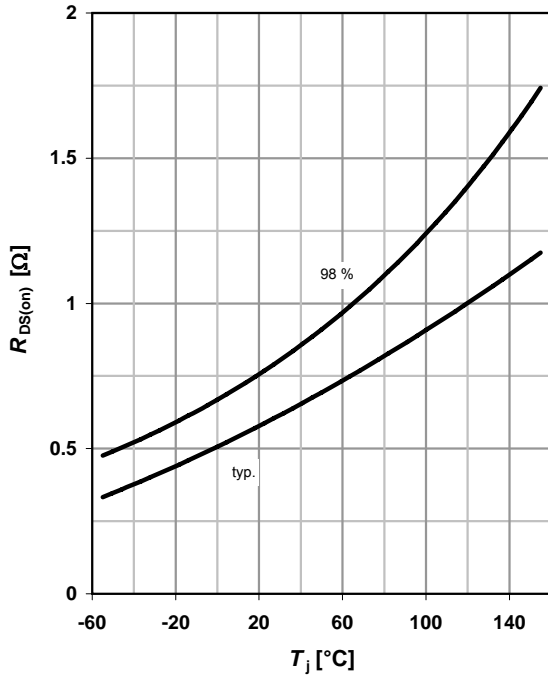
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



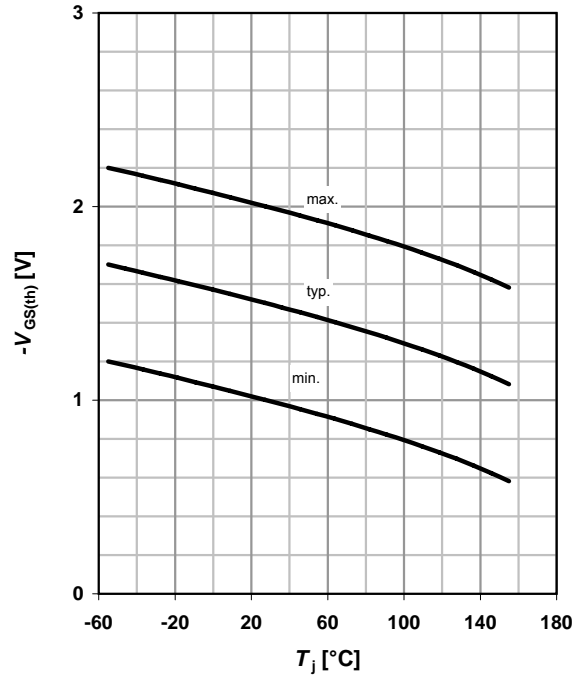
**9 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j); I_D = -1 \text{ A}; V_{GS} = -10 \text{ V}$



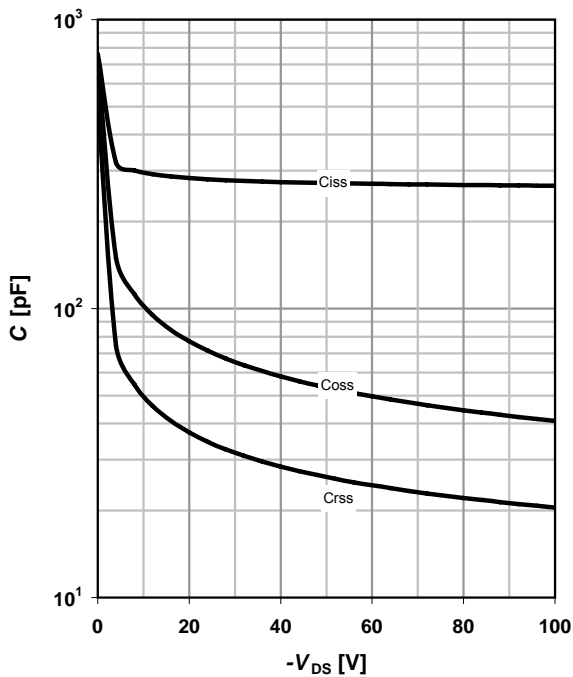
**10 Typ. gate threshold voltage**

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -380 \mu\text{A}$



**11 Typ. capacitances**

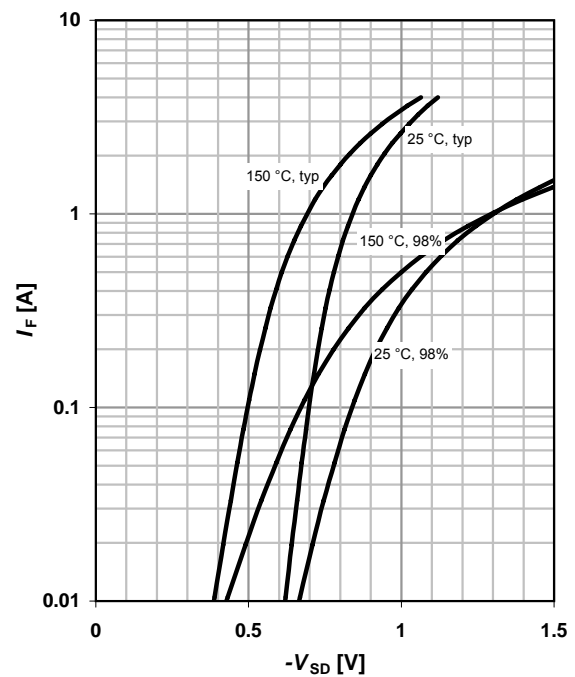
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

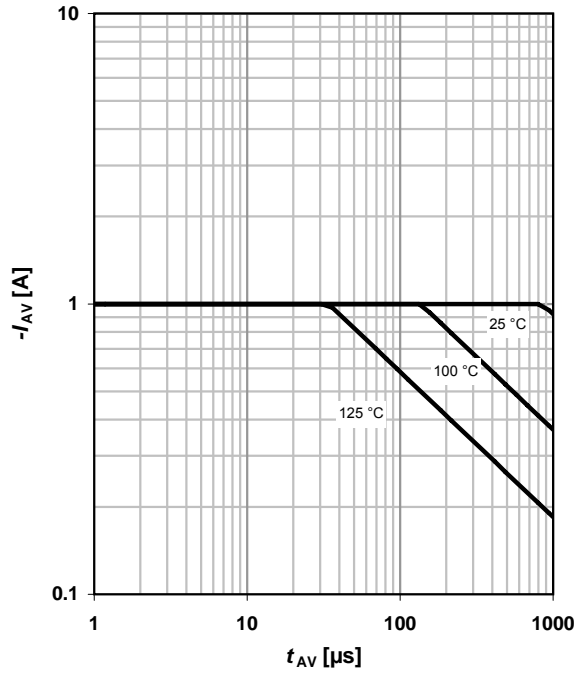
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$

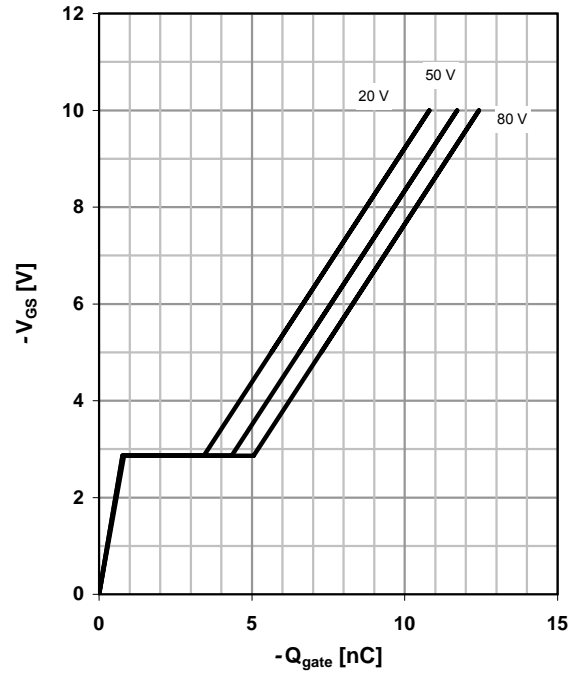
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

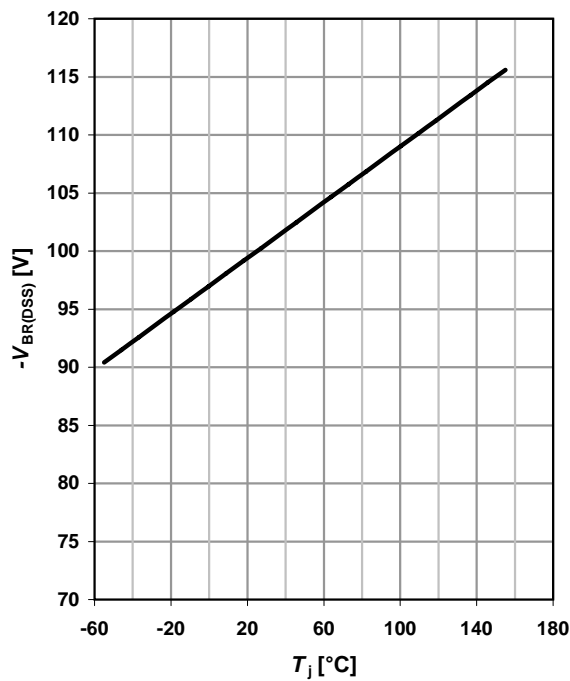
$V_{GS}=f(Q_{gate}); I_D=-1\ \text{A pulsed}$

parameter:  $V_{DD}$

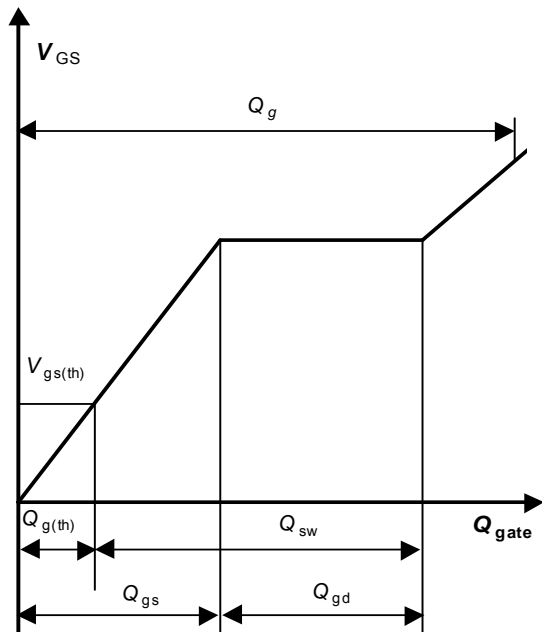


**15 Drain-source breakdown voltage**

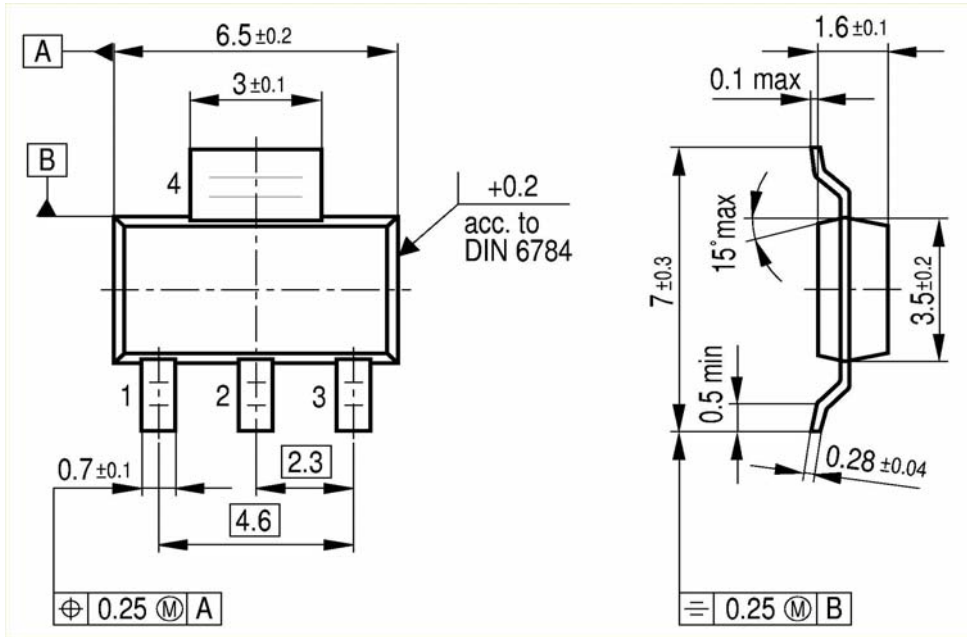
$V_{BR(DSS)}=f(T_j); I_D=-250\ \mu\text{A}$



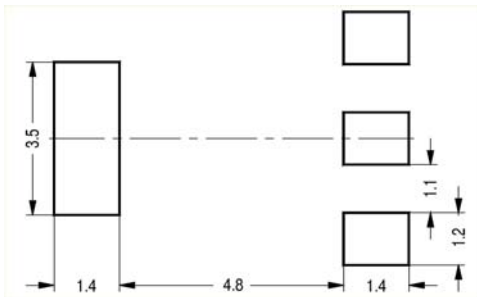
**16 Gate charge waveforms**



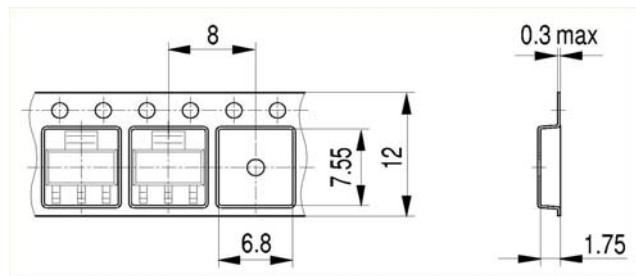
Package Outline: PG-SOT-223



Footprint:



Packaging:



Dimensions in mm



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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